

Silicon PNP Power Transistors

2SA1718

DESCRIPTION

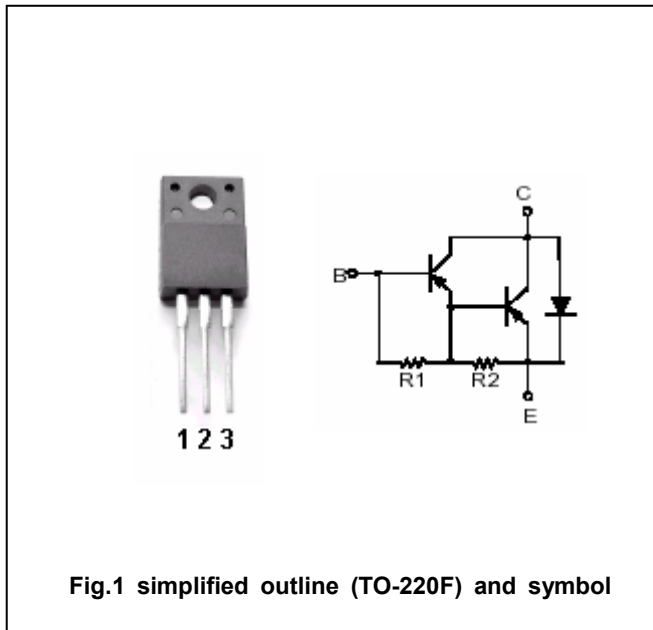
- With TO-220F package
- High DC current gain.
- Low collector saturation voltage.
- DARLINGTON

APPLICATIONS

- Ideal for motor drivers and solenoid drivers application

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-100	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-100	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-7	V
I <sub>C</sub>	Collector current		-5	A
I <sub>CM</sub>	Collector current-peak		-10	A
I <sub>B</sub>	Base current		-0.5	A
P <sub>C</sub>	Collector dissipation	T <sub>C</sub> =25°C	20	W
		T <sub>a</sub> =25°C	2.0	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-30mA; I <sub>B</sub> =0	-100			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-2A; I <sub>B</sub> =-2mA			-1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-2A; I <sub>B</sub> =-2mA			-2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-100V; I <sub>E</sub> =0			-10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-7V; I <sub>C</sub> =0			-5.0	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-2A; V <sub>CE</sub> =-2V	2000		20000	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-4A; V <sub>CE</sub> =-2V	500			

◆ h<sub>FE</sub> classifications

M	L	K
2000-5000	4000-10000	8000-20000

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PACKAGE OUTLINE

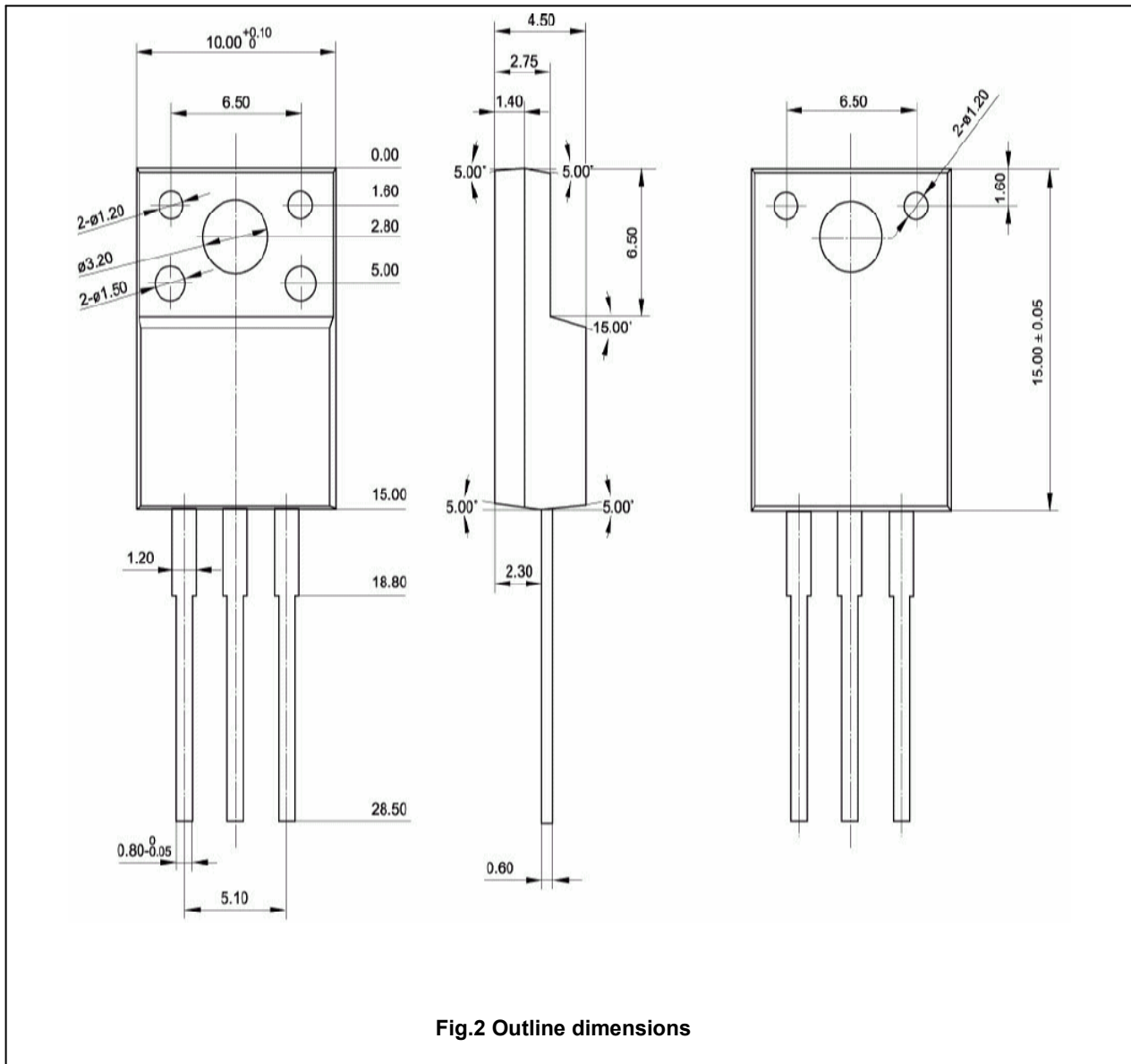


Fig.2 Outline dimensions